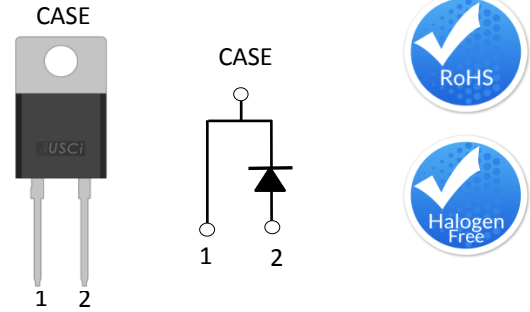


Description

United Silicon Carbide, Inc. offers the xR series of high performance SiC Schottky diodes. With zero reverse recovery charge and 175°C maximum junction temperature, USCi's diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ2D1215T	TO-220-2L	UJ2D1215T

Features

- ◆ Positive temperature coefficient for safe operation and ease of paralleling
- ◆ 175°C maximum operating junction temperature
- ◆ Extremely fast switching not dependent on temperature
- ◆ Essentially no reverse or forward recovery
- ◆ RoHS compliant

Typical Applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switching-mode power supplies
- ◆ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	V_R		1200	V
Repetitive peak reverse voltage, $T_j=25^\circ\text{C}$	V_{RRM}		1200	V
Surge peak reverse voltage	V_{RSM}		1200	V
Maximum DC forward current	I_F	$T_C = 138^\circ\text{C}$	15	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	112.5	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	90	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}, t_p = 10\text{ms}$	51.2	A
		$T_C = 110^\circ\text{C}, t_p = 10\text{ms}$	31.3	
Non-repetitive avalanche energy	E_{AS}	$T_j = 25^\circ\text{C}, L = 10\text{mH}, I_{pk}=5\text{A}, V_{DD}=100\text{V}$	132	mJ
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	187	W
		$T_C = 138^\circ\text{C}$	46	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	T_J, T_{STG}		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^\circ\text{C}$

Electrical Characteristics

T_J = +25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V _F	I _F = 15A, T _J = 25°C	-	1.5	1.7	V
		I _F = 15A, T _J = 175°C	-	2.5	3	
Reverse current	I _R	V _R =1200V, T _J =25°C	-	45	375	μA
		V _R =1200V, T _J =175°C	-	90	1000	
Total capacitive charge ⁽²⁾	Q _C	V _R =800V		69		nC
Total capacitance	C	V _R =1V, f=1MHz		730		pF
		V _R =400V, f=1MHz		64		
		V _R =800V, f=1MHz		51		
Capacitance stored energy	E _C	V _R =800V		17.5		μJ

(2) See Figure 8, Q_C is independent on T_J, di_F/dt, and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance	R _{θJC}			0.6	0.8	°C/W

Typical Performance

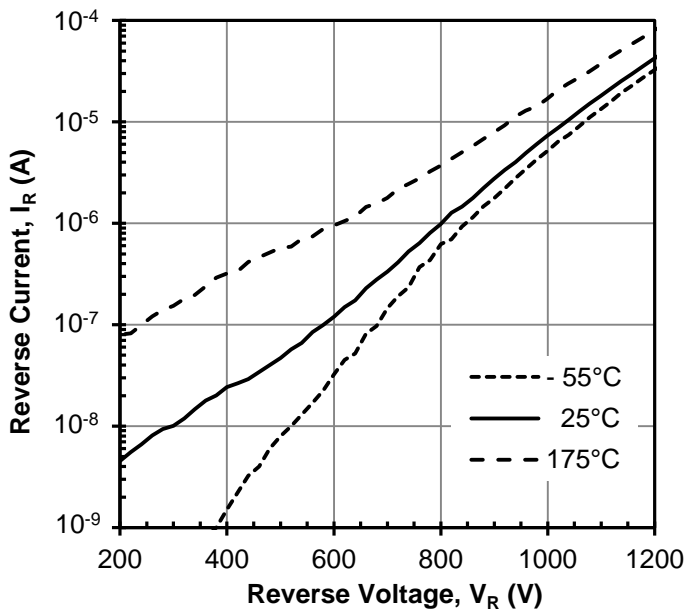


Figure 1 Typical reverse characteristics

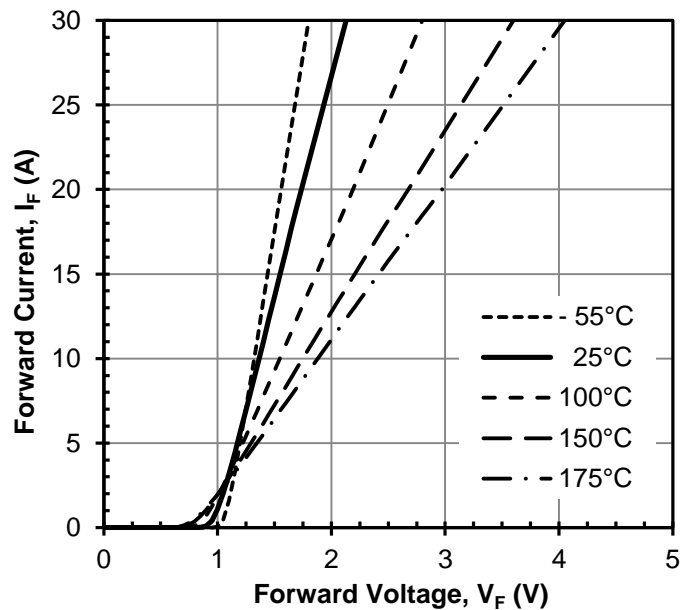


Figure 2 Typical forward characteristics

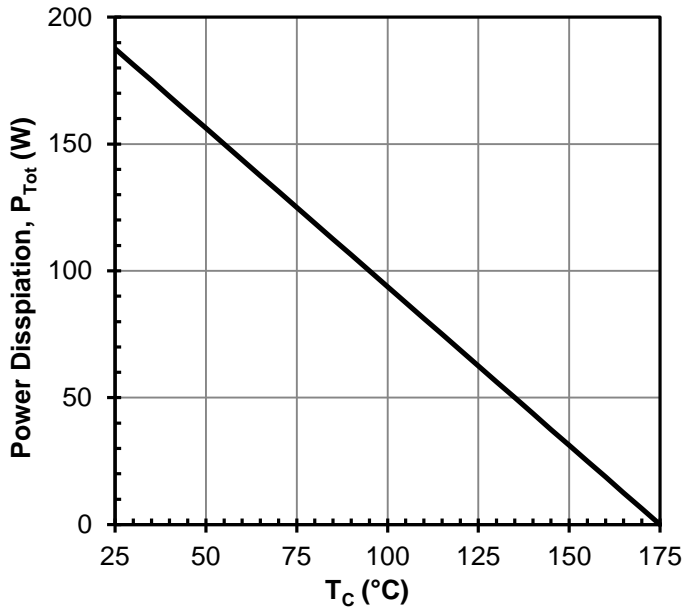


Figure 3 Power dissipation

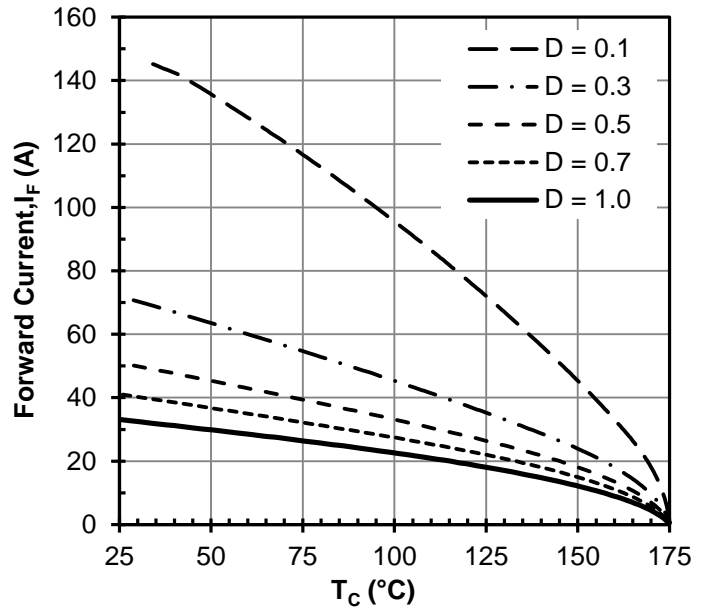


Figure 4 Diode forward current

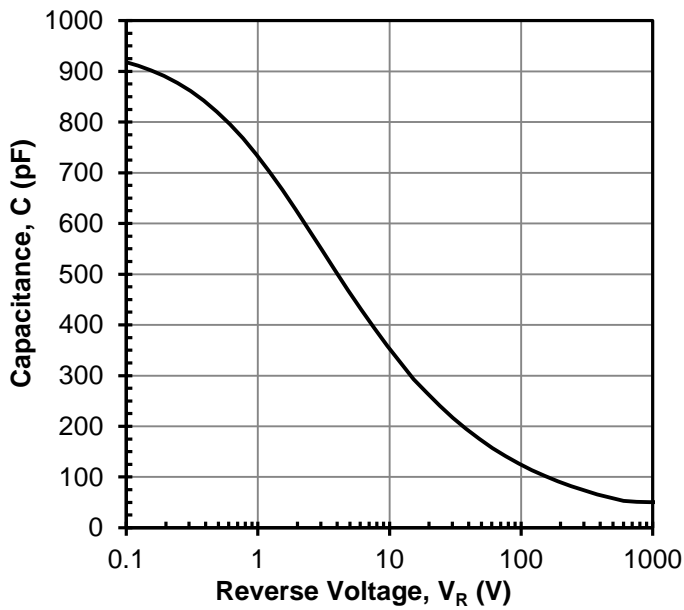


Figure 5 Capacitance vs. reverse voltage

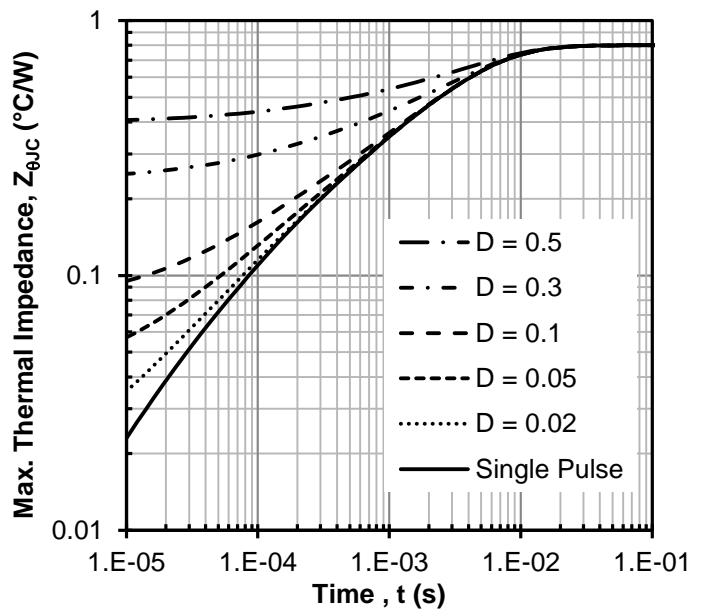


Figure 6 Maximum transient thermal impedance

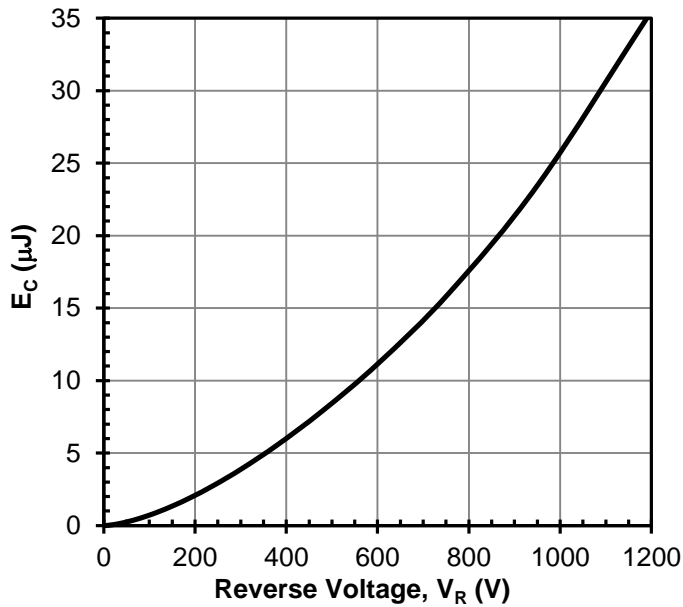


Figure 7 Typical capacitance stored energy vs. reverse voltage

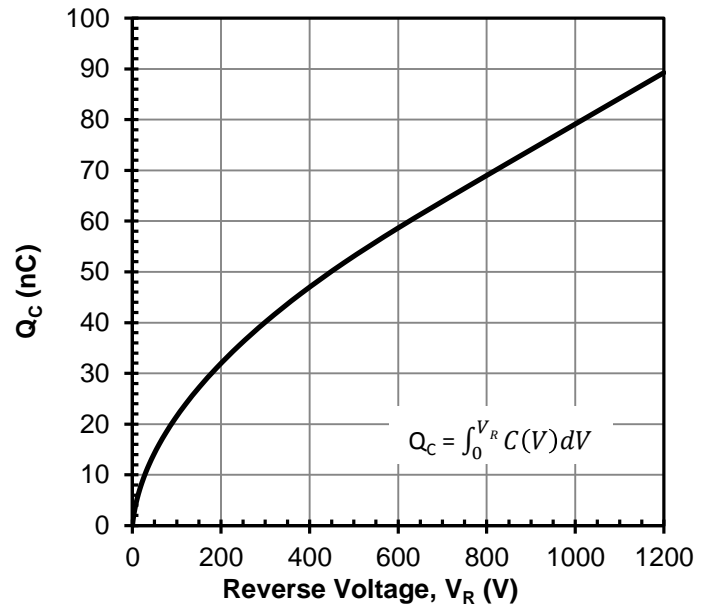


Figure 8 Typical capacitive charge vs. reverse voltage

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